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Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



PRODUCT SUMMARY			
I _{T(AV)}	110 A		
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V		
V _{TM}	1.57 V		
I _{GT}	80 mA		
TJ	-40 °C to +140 °C		
Package	TO-209AC (TO-94)		
Diode variation	Single SCR		

FEATURES

- High current and high surge ratings
- · Hermetic ceramic housing
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- · Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	А		
I _{T(AV)}	T _C	90	°C		
I _{T(RMS)}		172			
	50 Hz	2080	A		
I _{TSM}	60 Hz	2180			
l ² t	50 Hz	21.7	– kA ² s		
1-1	60 Hz	19.8	KA-S		
V _{DRM} /V _{RRM}		400 to 1200	V		
t _q	Typical	110	μs		
TJ		-40 to +140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA			
	40	400	500				
VS-110RKI VS-111RKI	80	800	900	20			
	120	1200	1300				

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RoHS COMPLIANT



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ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current		190° condu	otion half ains y		110	А
at case temperature	I _{T(AV)}	180 condu	ction, half sine	wave	90	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C	case temperat	ure	172	
		t = 10 ms	No voltage		2080	
Maximum peak, one-cycle	I	t = 8.3 ms	reapplied		2180	A
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1750	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1830	
Ma (an an 12) fact a (an		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	21.7	kA ² s
	l ² t	t = 8.3 ms reapplied	reapplied		19.8	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}		15.3	
		t = 8.3 ms	reapplied		14.0	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			217	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.82	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			1.02	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			2.16	
High level value of on-state slope resistance	r _{t2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			1.70	mΩ
Maximum on-state voltage	V _{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.57	V
Maximum holding current	Ι _Η	T 05 %C			200	
Typical latching current	١L	$T_J = 25 \text{ °C}$, anode supply 6 V resistive load 400		400	mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq$ 1 μs $T_J = T_J$ maximum, anode voltage \leq 80 % V_{DRM}	300	A/µs	
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/µs V _d = 0.67 % V _{DRM} , T _J = 25 °C	1	110	
Typical turn-off time	tq	I_{TM} = 50 A, T _J = T _J maximum, dl/dt = - 5 A/µs V _R = 50 V, dV/dt = 20 V/µs, gate 0 V 25 Ω	110	μs	

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA		



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TRIGGERING						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		VALUES		UNITS
PARAMETER	STIVIDUL			TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	12		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0	~~~
Maximum peak positive gate current	I _{GM}			3	.0	А
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms		0	v
Maximum peak negative gate voltage	- V _{GM}			10		
		T _J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA V
DC gate current required to trigger	I _{GT}	T _J = 25 °C		80	120	
		T _J = 140 °C		40	-	
		T _J = - 40 °C		2.5	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		1.6	2	
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	T. – T. movimum	Maximum gate current/ voltage not to trigger is the maximum value which will	6.0		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to +140	°C	
Maximum storage temperature range	T _{Stg}		-40 to +150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.27	K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1	rv/ VV	
Mounting torque + 10.0/		Non-lubricated threads	15.5 (137)	N·m	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet TO-209A		(TO-94)	

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.043	0.031				
120°	0.052	0.053				
90°	0.066	0.071	$T_J = T_J maximum$	K/W		
60°	0.096	0.101				
30°	0.167	0.169				

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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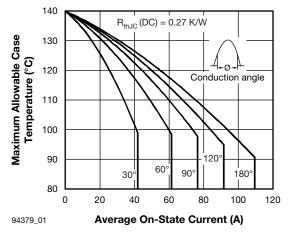


Fig. 1 - Current Ratings Characteristics

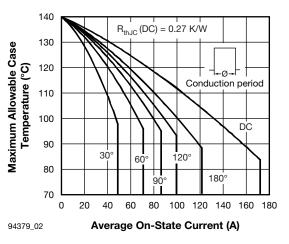


Fig. 2 - Current Ratings Characteristics

5 K/M

20

40

60

Maximum Allowable

Ambient Temperature (°C)

80

100

120

140

0

0

Vs

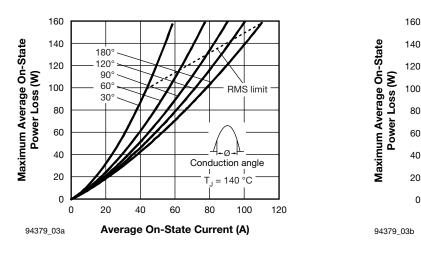
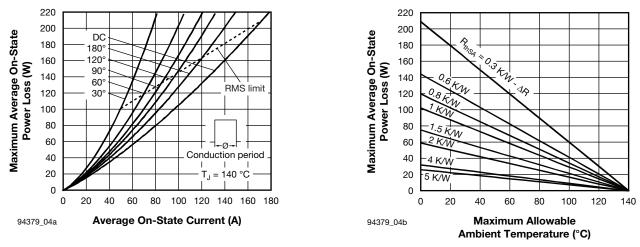


Fig. 3 - On-State Power Loss Characteristics





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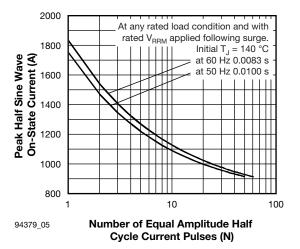


Fig. 5 - Maximum Non-Repetitive Surge Current

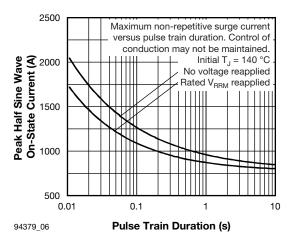


Fig. 6 - Maximum Non-Repetitive Surge Current

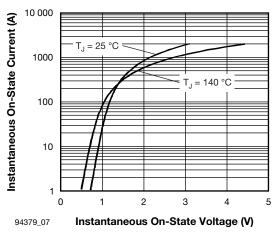
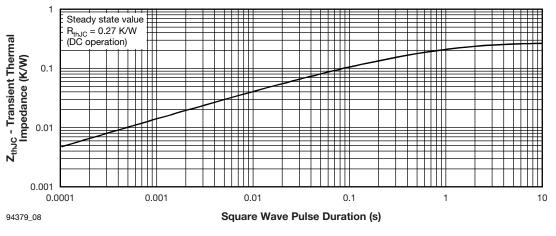


Fig. 7 - On-State Voltage Drop Characteristics





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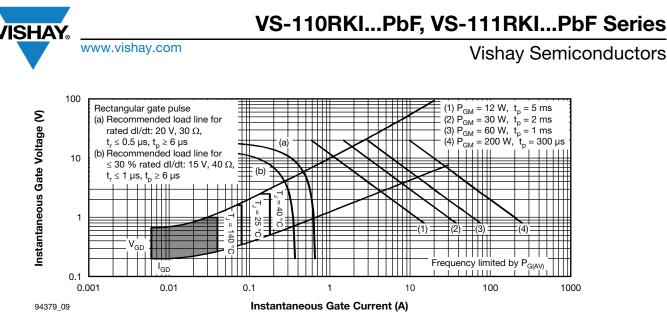


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code VS-
1 2 3 4 5 6

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95003			



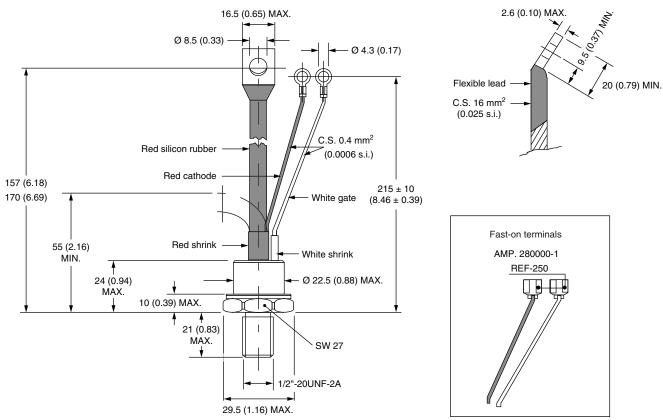
Vishay Semiconductors

TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)

SHA





Note

[•] For metric device: M12 x 1.75 contact factory



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